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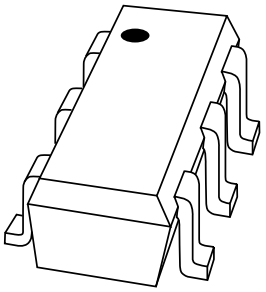
DATA SHEET



BF1205
Dual N-channel dual gate MOS-FET

Product specification

2003 Sep 30

Dual N-channel dual gate MOS-FET BF1205

FEATURES

- Two low noise gain controlled amplifiers in a single package. One with a fully integrated bias and one with a partly integrated bias
- Internal switch reduces the number of external components
- Superior cross-modulation performance during AGC
- High forward transfer admittance
- High forward transfer admittance to input capacitance ratio.

APPLICATIONS

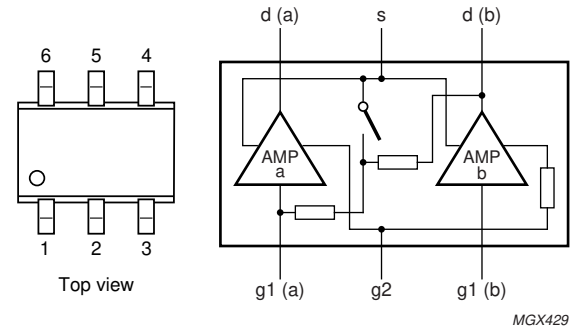
- Gain controlled low noise amplifiers for VHF and UHF applications with 5 V supply voltage, such as digital and analog television tuners and professional communications equipment.

DESCRIPTION

The BF1205 is a combination of two equal dual gate MOS-FET amplifiers with shared source and gate 2 leads and an integrated switch. The integrated switch is operated by the gate 1 bias of amplifier b. The source and substrate are interconnected. Internal bias circuits enable DC stabilization and a very good cross-modulation performance during AGC. Integrated diodes between the gates and source protect against excessive input voltage surges. The transistor is encapsulated in SOT363 micro-miniature plastic package.

PINNING - SOT363

PIN	DESCRIPTION
1	gate 1 (a)
2	gate 2
3	gate 1 (b)
4	drain (b)
5	source
6	drain (a)



Marking code: L4-.

Fig.1 Simplified outline and symbol.

ORDERING INFORMATION

TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
BF1205	–	Plastic surface mounted package; 6 leads	SOT363

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per MOS-FET; unless otherwise specified						
V_{DS}	drain-source voltage		–	–	10	V
I_D	drain current (DC)		–	–	30	mA
P_{tot}	total power dissipation	$T_s \leq 102$ °C; temperature at the soldering point of the source lead	–	–	200	mW
$\lvert y_{fs} \rvert$	forward transfer admittance	I_D = 12 mA	26	31	40	mS
$C_{ig1\text{-}ss}$	input capacitance at gate 1	amp. a: f = 1 MHz	–	1.8	2.3	pF
		amp. b: f = 1 MHz	–	2.0	2.5	pF
C_{rss}	reverse transfer capacitance	f = 1 MHz	–	20	–	fF
NF	noise figure	amp. a: f = 800 MHz	–	1.2	1.9	dB
		amp. b: f = 800 MHz	–	1.4	2.1	dB
X_{mod}	cross-modulation	amp. a: input level for k = 1% at 40 dB AGC	98	102	–	dBμV
		amp. b: input level for k = 1% at 40 dB AGC	100	105	–	dBμV
T_j	junction temperature		–	–	150	°C

CAUTION
This product is supplied in anti-static packing to prevent damage caused by electrostatic discharge during transport and handling.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per MOS-FET; unless otherwise specified					
V_{DS}	drain-source voltage		–	10	V
I_D	drain current (DC)		–	30	mA
I_{G1}	gate 1 current		–	±10	mA
I_{G2}	gate 2 current		–	±10	mA
P_{tot}	total power dissipation	$T_s \leq 102$ °C; note	–	200	mW
T_{stg}	storage temperature		−65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. T_s is the temperature at the soldering point of the source lead.

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	240	K/W

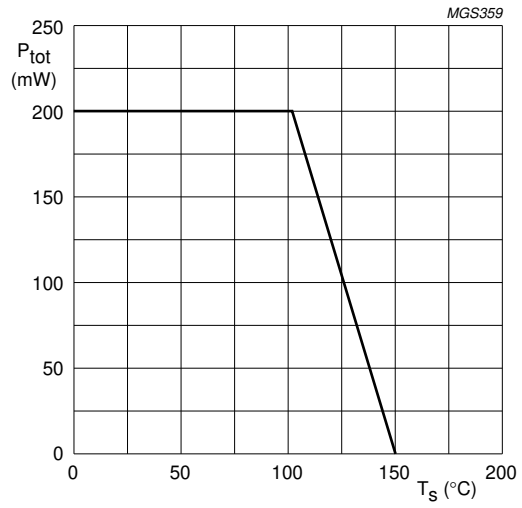


Fig.2 Power derating curve.

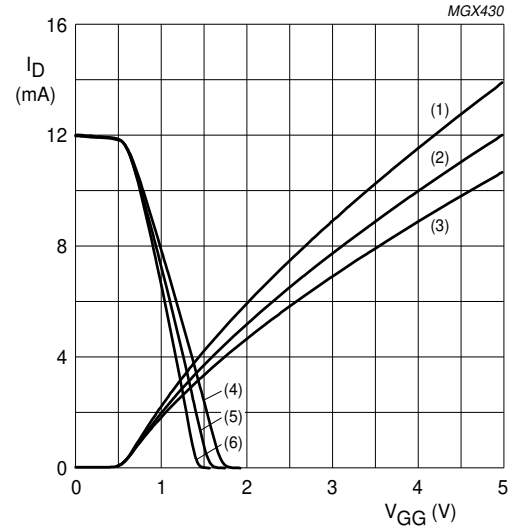
STATIC CHARACTERISTICS

T_j = 25 °C; per MOS-FET; unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)DSS}$	drain-source breakdown voltage	amp. a: V_{G1-S} = V_{G2-S} = 0 V; I_D = 10 μA	10	–	V
		amp. b: V_{G1-S} = V_{G2-S} = 0 V; I_D = 10 μA	7	–	V
$V_{(BR)G1-SS}$	gate-source breakdown voltage	V_{GS} = V_{DS} = 0 V; I_{G1-S} = 10 mA	6	10	V
$V_{(BR)G2-SS}$	gate-source breakdown voltage	V_{GS} = V_{DS} = 0 V; I_{G2-S} = 10 mA	6	10	V
$V_{(F)S-G1}$	forward source-gate voltage	V_{G2-S} = V_{DS} = 0 V; I_{S-G1} = 10 mA	0.5	1.5	V
$V_{(F)S-G2}$	forward source-gate voltage	V_{G1-S} = V_{DS} = 0 V; I_{S-G2} = 10 mA	0.5	1.5	V
$V_{G1-S(th)}$	gate-source threshold voltage	V_{DS} = 5 V; V_{G2-S} = 4 V; I_D = 100 μA	0.3	1	V
$V_{G2-S(th)}$	gate-source threshold voltage	V_{DS} = 5 V; V_{G1-S} = 5 V; I_D = 100 μA	0.4	1.0	V
I_{DSX}	drain-source current	amp. a: V_{G2-S} = 4 V; V_{DS} = 5 V; R_{G1} = 150 kΩ; note 1	8	16	mA
		amp. b: V_{G2-S} = 4 V; V_{DS} = 5 V; R_{G1} = 150 kΩ; note 2	8	16	mA
I_{G1-S}	gate cut-off current	amp. a: V_{G1-S} = 5 V; V_{G2-S} = V_{DS} = 0 V	–	50	nA
		amp. b: V_{G1-S} = 5 V; V_{G2-S} = V_{DS} = 0 V	–	50	nA
I_{G2-S}	gate cut-off current	V_{G2-S} = 4 V; V_{G1-S} = V_{DS} = 0 V	–	20	nA

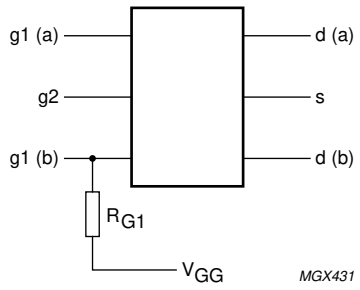
Note

1. R_{G1} connects gate 1 (b) to V_{GG} = 0 V (see Fig.4).
2. R_{G1} connects gate 1 (b) to V_{GG} = 5 V (see Fig.4).



(1) I_D (b); R_{G1} = 120 kΩ.
(2) I_D (b); R_{G1} = 150 kΩ.
(3) I_D (b); R_{G1} = 180 kΩ.
(4) I_D (a); R_{G1} = 180 kΩ.
(5) I_D (a); R_{G1} = 150 kΩ.
(6) I_D (a); R_{G1} = 120 kΩ.

Fig.3 Drain currents of MOS-FET a and b as functions of V_{GG} (see Fig.4).



V_{GG} = 5 V: amplifier a is OFF; amplifier b is ON.
V_{GG} = 0 V: amplifier a is ON; amplifier b is OFF.

Fig.4 Functional diagram

DYNAMIC CHARACTERISTICS AMPLIFIER a

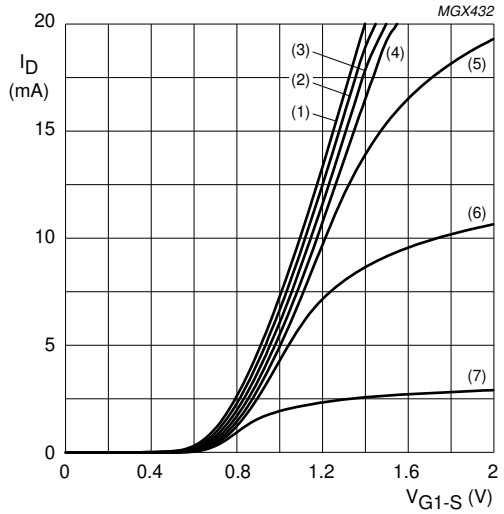
Common source; T_{amb} = 25 °C; V_{G2-S} = 4 V; V_{DS} = 5 V; I_D = 12 mA; note 1

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$\lvert y_{fs} \rvert$	forward transfer admittance	T_j = 25 °C	26	31	40	mS
C_{ig1-ss}	input capacitance at gate 1	f = 1 MHz	–	1.8	2.3	pF
C_{ig2-ss}	input capacitance at gate 2	f = 1 MHz	–	3.3	–	pF
C_{oss}	output capacitance	f = 1 MHz	–	0.75	–	pF
C_{rss}	reverse transfer capacitance	f = 1 MHz	–	20	–	fF
G_{tr}	power gain	f = 200 MHz; G_S = 2 mS; $B_S = B_{S(opt)}$; G_L = 0.5 mS; $B_L = B_{L(opt)}$	31	35	39	dB
		f = 400 MHz; G_S = 2 mS; $B_S = B_{S(opt)}$; G_L = 1 mS; $B_L = B_{L(opt)}$	27	31	35	dB
		f = 800 MHz; G_S = 3.3 mS; $B_S = B_{S(opt)}$; G_L = 1 mS; $B_L = B_{L(opt)}$	22	26	30	dB
NF	noise figure	f = 10.7 MHz; G_S = 20 mS; B_S = 0	–	4	–	dB
		f = 400 MHz; $Y_S = Y_{S(opt)}$	–	1.1	1.7	dB
		f = 800 MHz; $Y_S = Y_{S(opt)}$	–	1.2	1.9	dB
X_{mod}	cross-modulation	input level for k = 1% at 0 dB AGC; f_w = 50 MHz; f_{unw} = 60 MHz; note 2	90	–	–	dBμV
		input level for k = 1% at 10 dB AGC; f_w = 50 MHz; f_{unw} = 60 MHz; note 2	–	90	–	dBμV
		input level for k = 1% at 40 dB AGC; f_w = 50 MHz; f_{unw} = 60 MHz; note 2	98	102	–	dBμV

Notes

1. For the MOS-FET not in use: V_{G1-S} (b) = 0 V; V_{DS} (b) = 0 V.
2. Measured in Fig.13 test circuit.

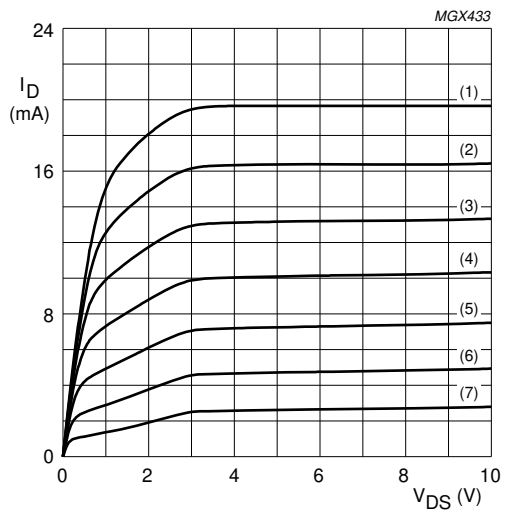
GRAPHS FOR AMPLIFIER a



(1) V_{G2-S} = 4 V.
(2) V_{G2-S} = 3.5 V.
(3) V_{G2-S} = 3 V.
(4) V_{G2-S} = 2.5 V.
(5) V_{G2-S} = 2 V.
(6) V_{G2-S} = 1.5 V.
(7) V_{G2-S} = 1 V.

V_{DS} (a) = 5 V; V_{G1-S} (b) = V_{DS} (b) = 0 V; T_j = 25 °C.

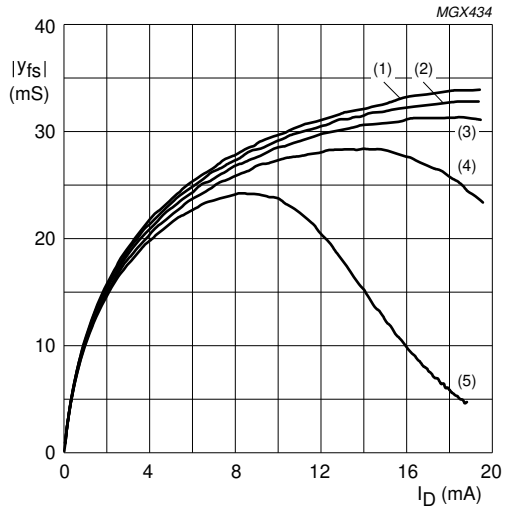
Fig.5 Transfer characteristics; typical values; amplifier a.



(1) V_{G1-S} (a) = 1.4 V.
(2) V_{G1-S} (a) = 1.3 V.
(3) V_{G1-S} (a) = 1.2 V.
(4) V_{G1-S} (a) = 1.1 V.
(5) V_{G1-S} (a) = 1 V.
(6) V_{G1-S} (a) = 0.9 V.
(7) V_{G1-S} (a) = 0.8 V.

V_{G2-S} = 4 V; V_{G1-S} (b) = V_{DS} (b) = 0 V; T_j = 25 °C.

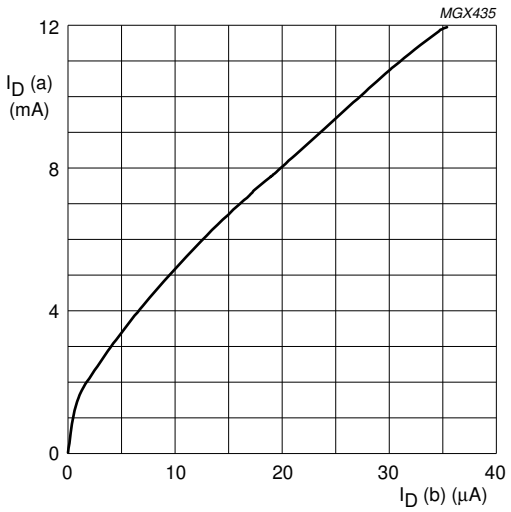
Fig.6 Output characteristics; typical values; amplifier a.



(1) $V_{G2\text{-}S}$ = 4 V.
(2) $V_{G2\text{-}S}$ = 3.5 V.
(3) $V_{G2\text{-}S}$ = 3 V.
(4) $V_{G2\text{-}S}$ = 2.5 V.
(5) $V_{G2\text{-}S}$ = 2 V.

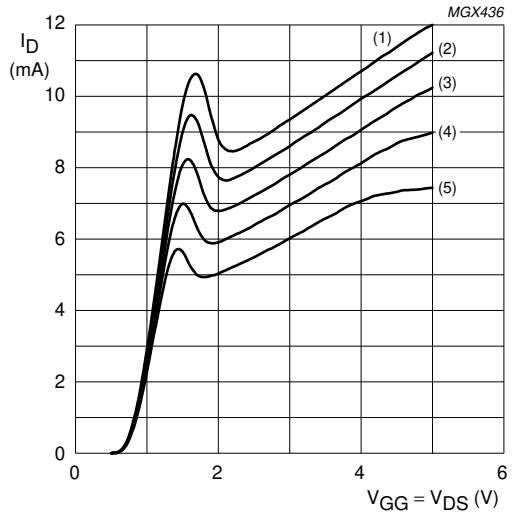
V_{DS} (a) = 5 V; $V_{G1\text{-}S}$ (b) = V_{DS} (b) = 0 V; T_j = 25 °C.

Fig.7 Forward transfer admittance as a function of drain current; typical values; amplifier a.



V_{DS} (a) = 5 V; $V_{G2\text{-}S}$ = 4 V; V_{DS} (b) = 5 V; $V_{G1\text{-}S}$ (b) = 0 V; T_j = 25 °C.

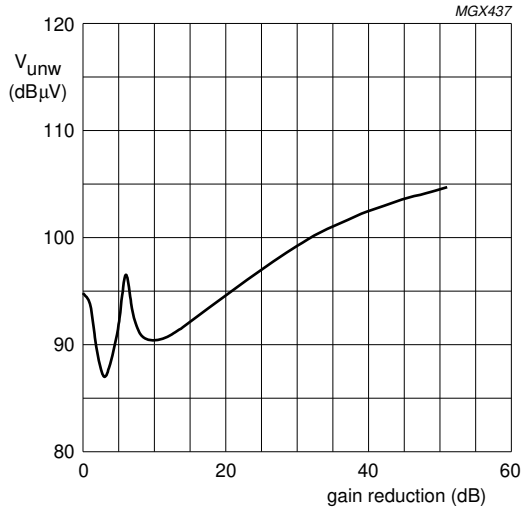
Fig.8 Drain current as a function of internal G1 current (current in pin drain (b) if MOS-FET (b) is switched off); typical values; amplifier a.



(1) V_{DS} (b) = 5 V.
(2) V_{DS} (b) = 4.5 V.
(3) V_{DS} (b) = 4 V.
(4) V_{DS} (b) = 3.5 V.
(5) V_{DS} (b) = 3 V.

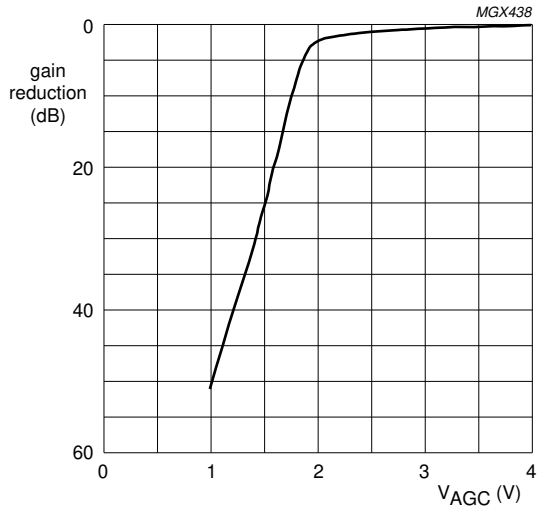
V_{DS} (a) = 5 V; $V_{G1\text{-}S}$ (b) = 0 V; Gate 1 (a) = open; T_j = 25 °C.

Fig.9 Drain current as a function of gate 2 and drain supply voltage; typical values; amplifier a.



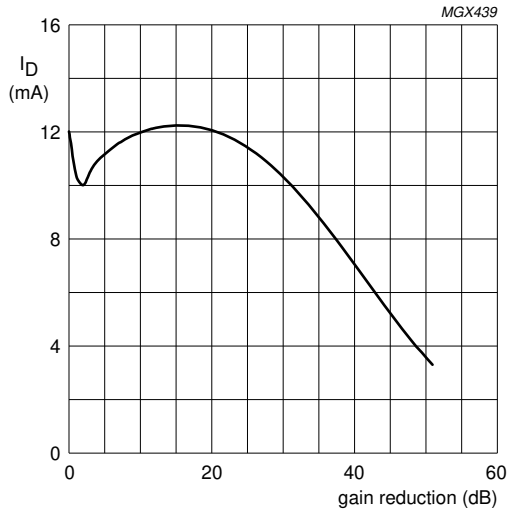
V_{DS} (a) = V_{DS} (b) = 5 V; $V_{G1\text{-}S}$ (b) = 0 V; f_w = 50 MHz; f_{unw} = 60 MHz; T_{amb} = 25 °C; see Fig.13.

Fig.10 Unwanted voltage for 1% cross-modulation as a function of gain reduction; typical values; amplifier a.



V_{DS} (a) = V_{DS} (b) = 5 V; $V_{G1\text{-}S}$ (b) = 0 V; f = 50 MHz; see Fig.13.

Fig.11 Gain reduction as a function of AGC voltage; typical values; amplifier a.



V_{DS} (a) = V_{DS} (b) = 5 V; $V_{G1\text{-}S}$ (b) = 0 V; f = 50 MHz; T_{amb} = 25 °C; see Fig.13.

Fig.12 Drain current as a function of gain reduction; typical values; amplifier a.

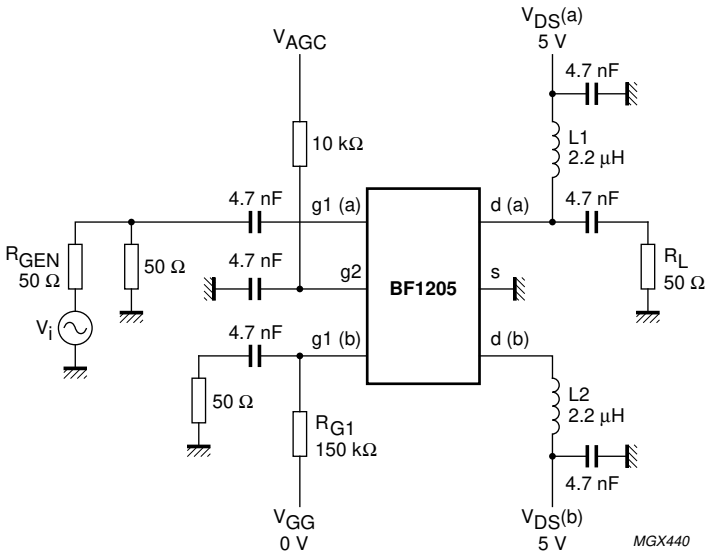
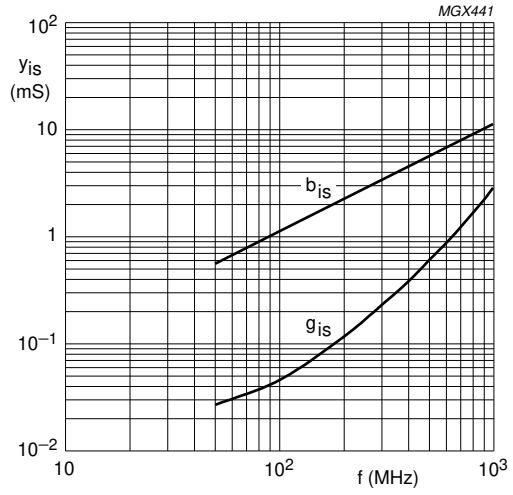
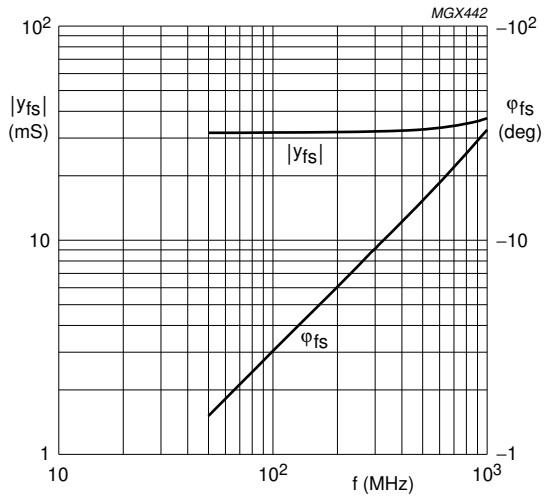


Fig.13 Cross-modulation test set-up for amplifier a.



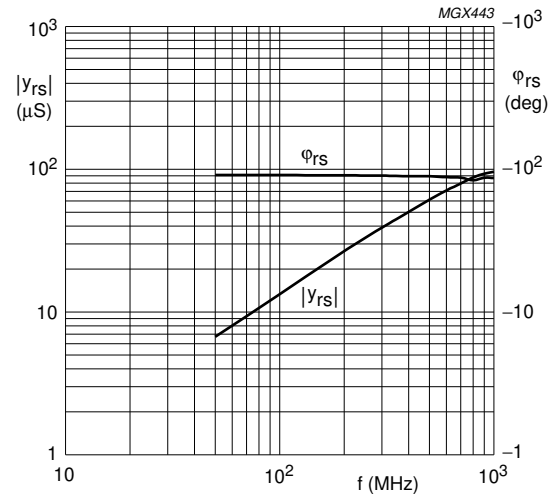
V_{DS} (a) = 5 V; $V_{G2\text{-}S}$ (a) = 4 V; V_{DS} (b) = $V_{G1\text{-}S}$ (b) = 0 V;
I_D (a) = 12 mA.

Fig.14 Input admittance as a function of frequency; typical values; amplifier a.



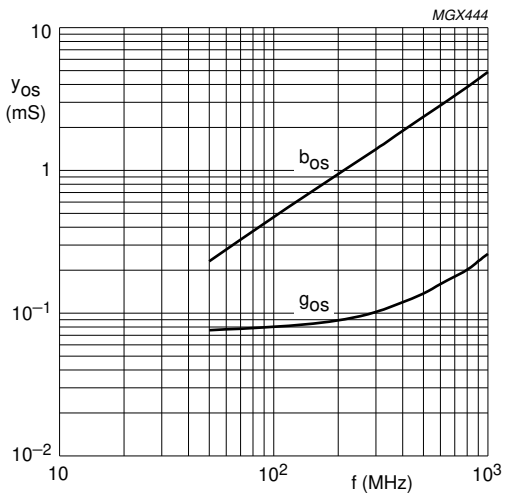
V_{DS} (a) = 5 V; $V_{G2\text{-}S}$ (a) = 4 V; V_{DS} (b) = $V_{G1\text{-}S}$ (b) = 0 V;
I_D (a) = 12 mA.

Fig.15 Forward transfer admittance and phase as a function of frequency; typical values; amplifier a.



V_{DS} (a) = 5 V; $V_{G2\text{-}S}$ (a) = 4 V; V_{DS} (b) = $V_{G1\text{-}S}$ (b) = 0 V;
I_D (a) = 12 mA.

Fig.16 Reverse transfer admittance and phase as a function of frequency; typical values; amplifier a.



V_{DS} (a) = 5 V; $V_{G2\text{-}S}$ (a) = 4 V; V_{DS} (b) = $V_{G1\text{-}S}$ (b) = 0 V;
I_D (a) = 12 mA.

Fig.17 Output admittance as a function of frequency; typical values; amplifier a.

Scattering parameters: amplifier a

V_{DS} (a) = 5 V; $V_{G2\text{-}S}$ = 4 V; I_D (a) = 12 mA; V_{DS} (b) = 0 V; $V_{G\text{-}1S}$ (b) = 0 V; T_{amb} = 25 °C

f (MHz)	s_{11}		s_{21}		s_{12}		s_{22}	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
50	0.997	−3.70	3.15	175.99	0.00067	86.39	0.992	−1.38
100	0.995	−7.37	3.15	171.92	0.00132	84.34	0.991	−2.83
200	0.988	−14.64	3.12	163.99	0.00262	79.71	0.990	−5.62
300	0.976	−21.85	3.09	156.06	0.00373	75.29	0.988	−8.40
400	0.963	−28.95	3.04	148.32	0.00471	71.43	0.985	−11.15
500	0.944	−35.98	2.99	140.52	0.00557	66.89	0.982	−13.88
600	0.924	−42.90	2.94	132.88	0.00624	63.52	0.978	−16.65
700	0.900	−49.77	2.87	125.30	0.00669	60.09	0.975	−19.35
800	0.874	−56.61	2.81	117.79	0.00701	59.58	0.972	−22.08
900	0.846	−63.18	2.73	110.29	0.00705	52.42	0.968	−24.87
1000	0.817	−69.84	2.65	102.91	0.00688	49.17	0.965	−27.63

Noise data

V_{DS} (a) = 5 V; $V_{G2\text{-}S}$ = 4 V; I_D (a) = 12 mA; V_{DS} (b) = 0 V; $V_{G\text{-}1S}$ (b) = 0 V; T_{amb} = 25 °C

f (MHz)	F MIN (dB)	GAMMA OPT		Rn (Ω)
		(ratio)	(deg)	
400	1.1	0.719	16.16	31.18
800	1.2	0.628	32.7	29.74

DYNAMIC CHARACTERISTICS AMPLIFIER b

Common source; T_{amb} = 25 °C; $V_{G2\text{-}S}$ = 4 V; V_{DS} = 5 V; I_D = 12 mA

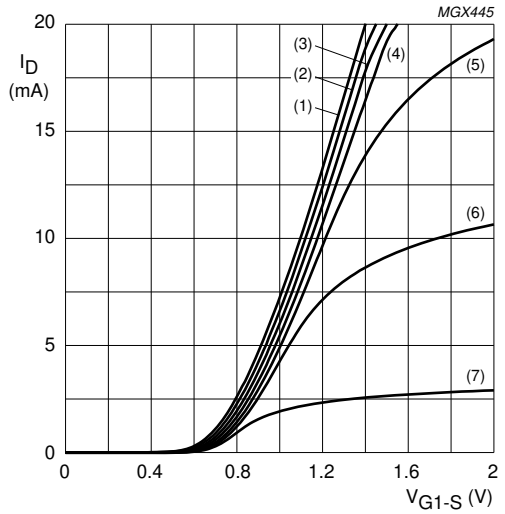
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$\lvert y_{fs} \rvert$	forward transfer admittance	T_j = 25 °C	26	31	40	mS
$C_{ig1\text{-}ss}$	input capacitance at gate 1	f = 1 MHz	–	2.0	2.5	pF
$C_{ig2\text{-}ss}$	input capacitance at gate 2	f = 1 MHz	–	3.3	–	pF
C_{oss}	output capacitance	f = 1 MHz	–	0.85	–	pF
C_{rss}	reverse transfer capacitance	f = 1 MHz	–	20	–	fF
G_{tr}	power gain	f = 200 MHz; G_S = 2 mS; $B_S = B_{S(opt)}$; G_L = 0.5 mS; $B_L = B_{L(opt)}$; note 1	30	34	38	dB
		f = 400 MHz; G_S = 2 mS; $B_S = B_{S(opt)}$; G_L = 1 mS; $B_L = B_{L(opt)}$; note 1	27	31	35	dB
		f = 800 MHz; G_S = 3.3 mS; $B_S = B_{S(opt)}$; G_L = 1 mS; $B_L = B_{L(opt)}$; note 1	22	26	30	dB
NF	noise figure	f = 10.7 MHz; G_S = 20 mS; B_S = 0	–	4	–	dB
		f = 400 MHz; $Y_S = Y_{S(opt)}$	–	1.3	1.9	dB
		f = 800 MHz; $Y_S = Y_{S(opt)}$	–	1.4	2.1	dB

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
X_{mod}	cross-modulation	input level for k = 1% at 0 dB AGC; f_w = 50 MHz; f_{unw} = 60 MHz; note 2	90	–	–	dBμV
		input level for k = 1% at 10 dB AGC; f_w = 50 MHz; f_{unw} = 60 MHz; note 2	–	92	–	dBμV
		input level for k = 1% at 40 dB AGC; f_w = 50 MHz; f_{unw} = 60 MHz; note 2	100	105	–	dBμV

Notes

1. For the MOS-FET not in use: $V_{G1\text{-}S}$ (a) = 0; V_{DS} (a) = 0.
2. Measured in test circuit Fig.30.

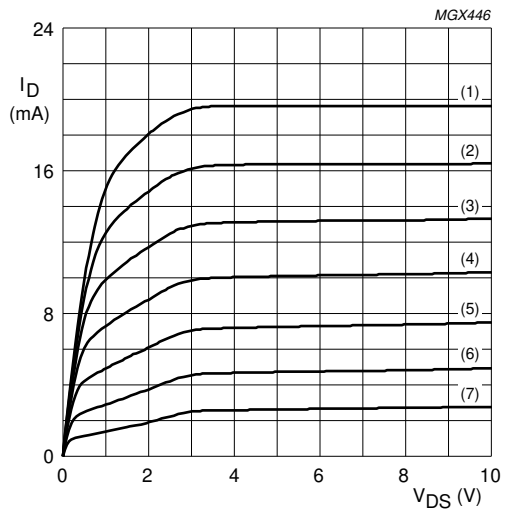
GRAPHS FOR AMPLIFIER b



(1) $V_{G2\text{-}S}$ = 4 V.
(2) $V_{G2\text{-}S}$ = 3.5 V.
(3) $V_{G2\text{-}S}$ = 3 V.
(4) $V_{G2\text{-}S}$ = 2.5 V.
(5) $V_{G2\text{-}S}$ = 2 V.
(6) $V_{G2\text{-}S}$ = 1.5 V.
(7) $V_{G2\text{-}S}$ = 1 V.

V_{DS} (b) = 5 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V; T_j = 25 °C.

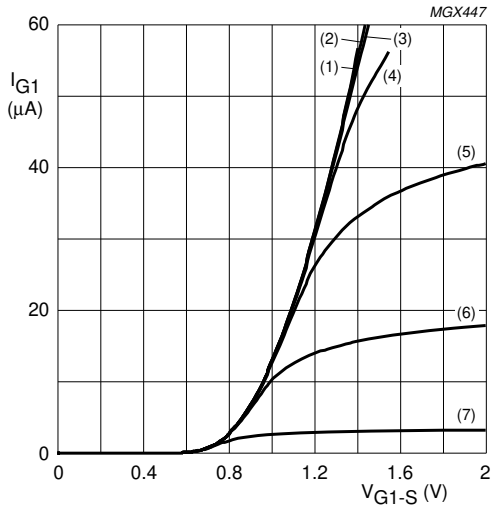
Fig.18 Transfer characteristics; typical values; amplifier b.



(1) $V_{G1\text{-}S}$ (b) = 1.4 V.
(2) $V_{G1\text{-}S}$ (b) = 1.3 V.
(3) $V_{G1\text{-}S}$ (b) = 1.2 V.
(4) $V_{G1\text{-}S}$ (b) = 1.1 V.
(5) $V_{G1\text{-}S}$ (b) = 1 V.
(6) $V_{G1\text{-}S}$ (b) = 0.9 V.
(7) $V_{G1\text{-}S}$ (b) = 0.8 V.

$V_{G2\text{-}S}$ = 4 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V; T_j = 25 °C.

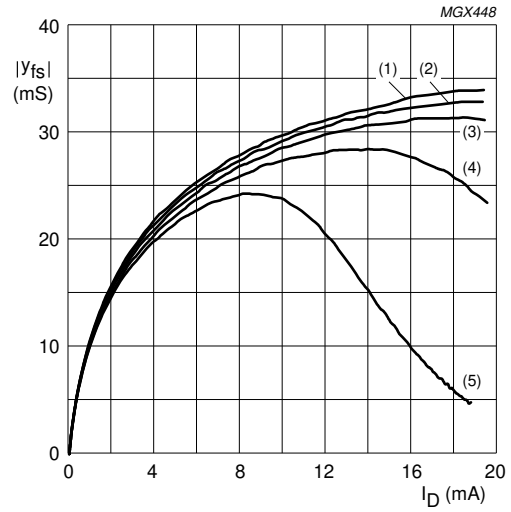
Fig.19 Output characteristics; typical values; amplifier b.



(1) V_{G2-S} = 4 V.
(2) V_{G2-S} = 3.5 V.
(3) V_{G2-S} = 3 V.
(4) V_{G2-S} = 2.5 V.
(5) V_{G2-S} = 2 V.
(6) V_{G2-S} = 1.5 V.
(7) V_{G2-S} = 1 V.

V_{DS} (b) = 5 V; V_{DS} (a) = V_{G1-S} (a) = 0 V; T_j = 25 °C.

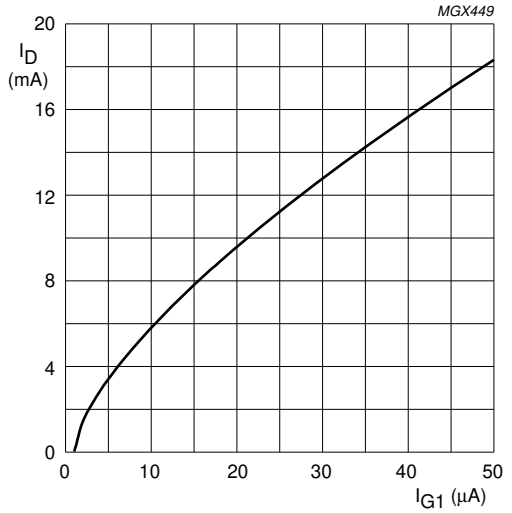
Fig.20 Gate 1 current as a function of gate 1 voltage; typical values; amplifier b.



(1) V_{G2-S} = 4 V.
(2) V_{G2-S} = 3.5 V.
(3) V_{G2-S} = 3 V.
(4) V_{G2-S} = 2.5 V.
(5) V_{G2-S} = 2 V.

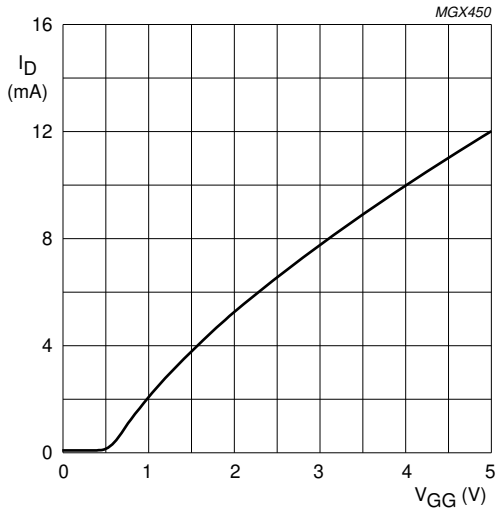
V_{DS} (b) = 5 V; V_{DS} (a) = V_{G1-S} (a) = 0 V; T_j = 25 °C.

Fig.21 Forward transfer admittance as a function of drain current; typical values; amplifier b.



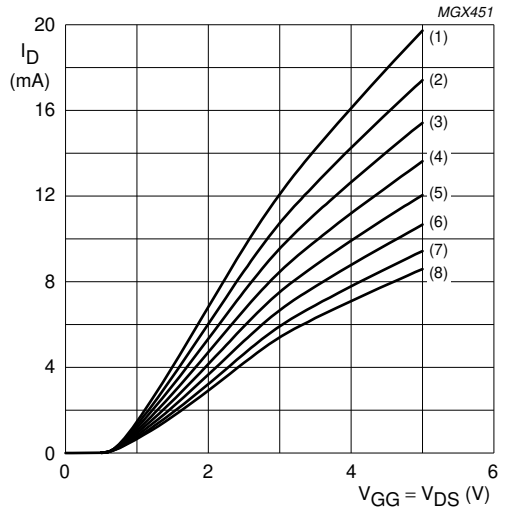
V_{DS} (b) = 5 V; $V_{G2\text{-}S}$ = 4 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V; T_j = 25 °C.

Fig.22 Drain current as a function of gate 1 current; typical values; amplifier b.



V_{DS} (b) = 5 V; $V_{G2\text{-}S}$ = 4 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V;
T_j = 25 °C; R_{G1} (b) = 150 kΩ (connected to V_{GG}); see Fig.4.

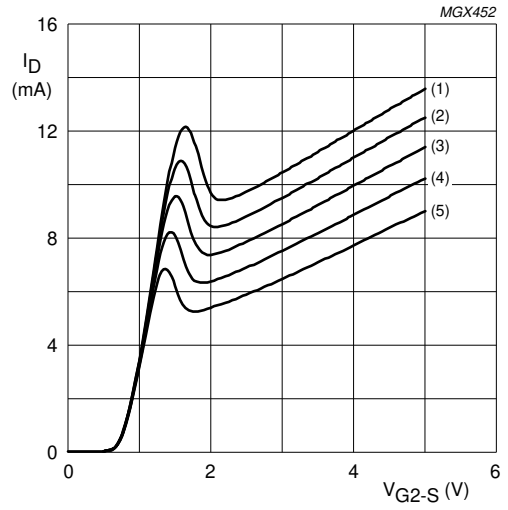
Fig.23 Drain current as a function of gate 1 supply voltage (V_{GG}); typical values; amplifier b.



(1) R_{G1} (b) = 68 kΩ.
(2) R_{G1} (b) = 82 kΩ.
(3) R_{G1} (b) = 100 kΩ.
(4) R_{G1} (b) = 120 kΩ.
(5) R_{G1} (b) = 150 kΩ.
(6) R_{G1} (b) = 180 kΩ.
(7) R_{G1} (b) = 220 kΩ.
(8) R_{G1} (b) = 270 kΩ.

V_{G2-S} = 4 V; V_{DS} (a) = V_{G1-S} (a) = 0 V; T_j = 25 °C;
R_{G1} (b) = 150 kΩ (connected to V_{GG}); see Fig.4.

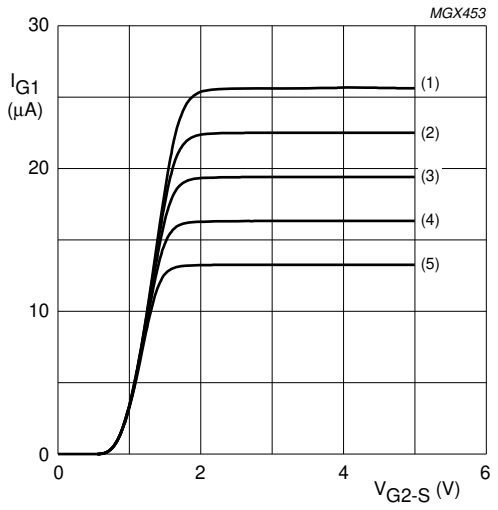
Fig.24 Drain current as a function of gate 1 (V_{GG}) and drain supply voltage; typical values; amplifier b.



(1) V_{GG} = 5.0 V.
(2) V_{GG} = 4.5 V.
(3) V_{GG} = 4.0 V.
(4) V_{GG} = 3.5 V.
(5) V_{GG} = 3.0 V.

V_{DS} (b) = 5 V; V_{DS} (a) = V_{G1-S} (a) = 0 V; T_j = 25 °C;
R_{G1} (b) = 150 kΩ (connected to V_{GG}); see Fig.4.

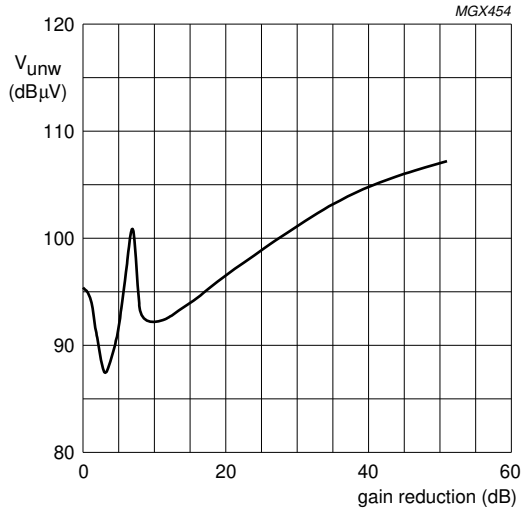
Fig.25 Drain current as a function of gate 2 voltage; typical values; amplifier b.



(1) V_{GG} = 5.0 V.
(2) V_{GG} = 4.5 V.
(3) V_{GG} = 4.0 V.
(4) V_{GG} = 3.5 V.
(5) V_{GG} = 3.0 V.

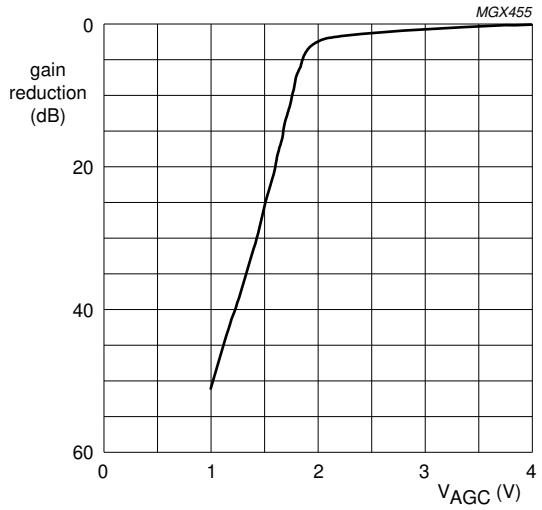
V_{DS} (b) = 5 V; V_{DS} (a) = V_{G1-S} (a) = 0 V; T_j = 25 °C;
R_{G1} (b) = 150 kΩ (connected to V_{GG}); see Fig.4.

Fig.26 Gate 1 current as a function of gate 2 voltage; typical values; amplifier b.



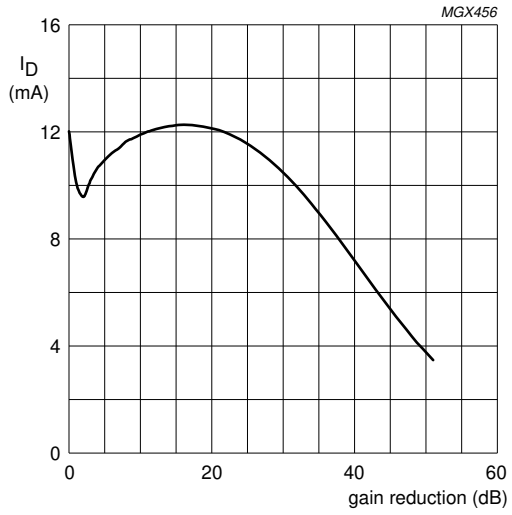
V_{DS} (b) = 5 V; V_{GG} = 5 V; V_{DS} (a) = V_{G1-S} (a) = 0 V;
R_{G1} (b) = 150 kΩ (connected to V_{GG}); f_w = 50 MHz;
f_{unw} = 60 MHz; T_{amb} = 25 °C; see Fig.30.

Fig.27 Unwanted voltage for 1% cross-modulation as a function of gain reduction; typical values; amplifier b.



V_{DS} (b) = 5 V; V_{GG} = 5 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V;
R_{G1} (b) = 150 kΩ (connected to V_{GG}); f = 50 MHz;
T_{amb} = 25 °C; see Fig.30.

Fig.28 Typical gain reduction as a function of AGC voltage; amplifier b.



V_{DS} (b) = 5 V; V_{GG} = 5 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V;
R_{G1} (b) = 150 kΩ (connected to V_{GG}); f = 50 MHz;
T_{amb} = 25 °C; see Fig.30.

Fig.29 Drain current as a function of gain reduction; typical values; amplifier b.

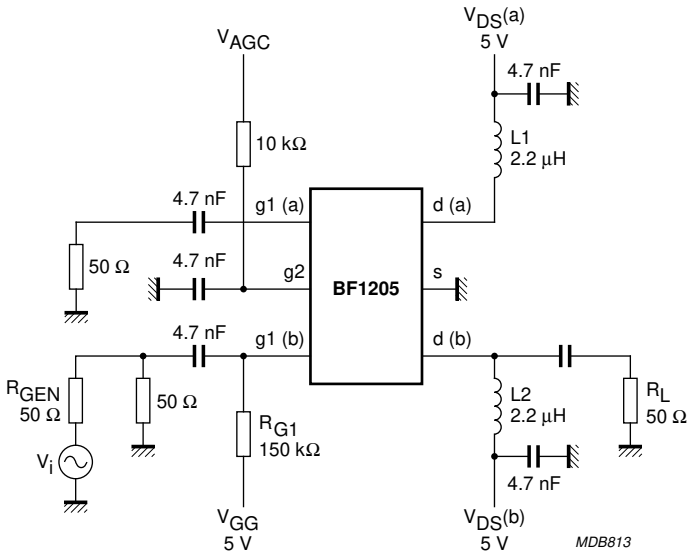
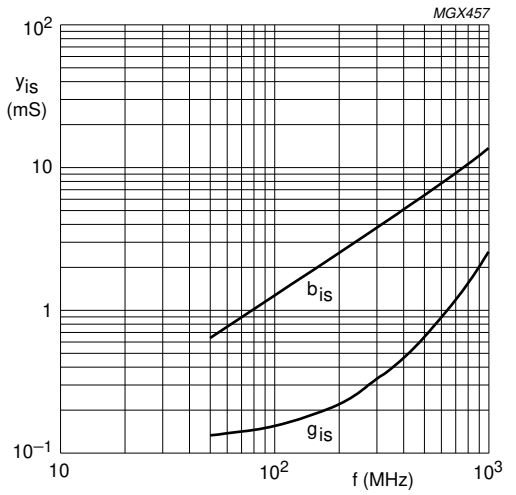
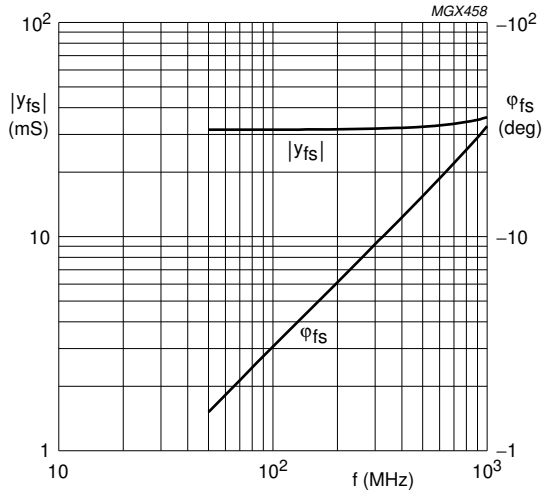


Fig.30 Cross-modulation test set-up for amplifier b.



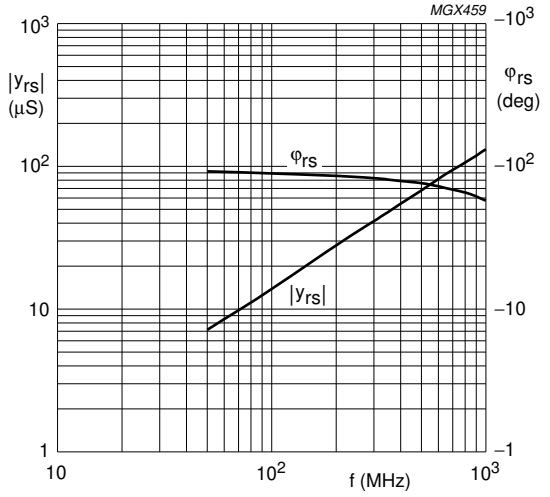
V_{DS} (b) = 5 V; $V_{G2\text{-}S}$ = 4 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V;
I_D (b)= 12 mA.

Fig.31 Input admittance as a function of frequency; typical values; amplifier b.



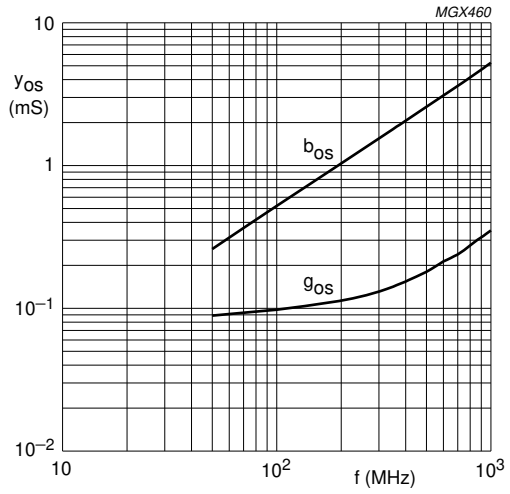
V_{DS} (b) = 5 V; $V_{G2\text{-}S}$ = 4 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V;
I_D (b) = 12 mA.

Fig.32 Forward transfer admittance and phase as a function of frequency; typical values; amplifier b.



V_{DS} (b) = 5 V; $V_{G2\text{-}S}$ = 4 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V;
I_D (b) = 12 mA.

Fig.33 Reverse transfer admittance and phase as a function of frequency; typical values; amplifier b.



V_{DS} (b) = 5 V; $V_{G2\text{-}S}$ = 4 V; V_{DS} (a) = $V_{G1\text{-}S}$ (a) = 0 V;
I_D (b) = 12 mA.

Fig.34 Output admittance as a function of frequency; typical values; amplifier b.

Scattering parameters: amplifier b

V_{DS} (b) = 5 V; $V_{G2\text{-}S}$ = 4 V; I_D (b) = 12 mA; V_{DS} (a) = 0 V; $V_{G1\text{-}S}$ (a) = 0 V; T_{amb} = 25 °C

f (MHz)	s_{11}		s_{21}		s_{12}		s_{22}	
	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)	MAGNITUDE (ratio)	ANGLE (deg)
50	0.987	−3.76	3.12	175.87	0.00071	85.43	0.991	−1.56
100	0.985	−7.38	3.11	171.77	0.00136	86.06	0.989	−3.11
200	0.978	−14.63	3.09	163.72	0.00272	84.25	0.988	−6.16
300	0.968	−21.82	3.06	155.67	0.00396	82.63	0.986	−9.17
400	0.956	−28.92	3.01	147.79	0.00509	81.35	0.983	−12.17
500	0.941	−35.99	2.95	139.86	0.00616	79.46	0.973	−15.16
600	0.924	−42.93	2.89	132.06	0.00710	78.57	0.975	−18.15
700	0.905	−49.89	2.83	124.31	0.00791	77.88	0.972	−21.07
800	0.884	−56.57	2.75	116.69	0.00848	76.72	0.968	−24.08
900	0.861	−63.36	2.67	108.97	0.00900	76.55	0.964	−27.03
1000	0.837	−70.05	2.59	101.39	0.00941	76.67	0.959	−30.02

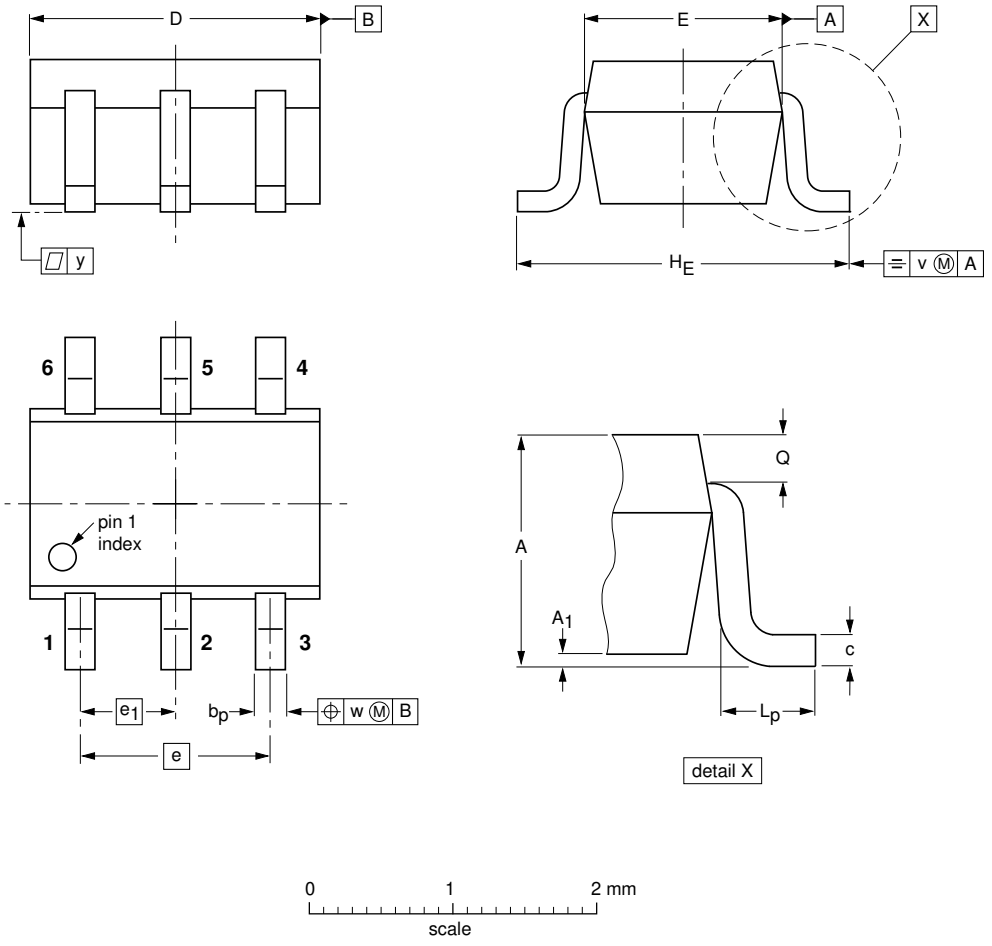
Noise data

V_{DS} (b) = 5 V; $V_{G2\text{-}S}$ = 4 V; I_D (b) = 12 mA; V_{DS} (a) = 0 V; $V_{G1\text{-}S}$ (a) = 0 V; T_{amb} = 25 °C

f (MHz)	F MIN (dB)	F MIN (dB)		R_n (Ω)
		(ratio)	(deg)	
400	1.3	0.662	16.76	31.55
800	1.4	0.578	33.97	30.53

PACKAGE OUTLINE

Plastic surface-mounted package; 6 leads **SOT363**



DIMENSIONS (mm are the original dimensions)

UNIT	A	A_1 max	b_p	c	D	E	e	e_1	H_E	L_p	Q	v	w	y
mm	1.1 0.8	0.1	0.30 0.20	0.25 0.10	2.2 1.8	1.35 1.15	1.3	0.65	2.2 2.0	0.45 0.15	0.25 0.15	0.2	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT363			SC-88			~~04-11-08~~ 06-03-16

DATA SHEET STATUS

DOCUMENT STATUS[1]	PRODUCT STATUS[2]	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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